

Inventor Information

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Application Information

Title Line One:: A METHOD FOR FORMING CRYSTALLINE
Title Line Two:: SEMICONDUCTOR LAYERS, A METHOD FOR
Title Line Three:: FABRICATING THIN FILM TRANSISTORS,
Title Line Four:: AND A METHOD FOR FABRICATING SOLAR
Title Line Five:: CELLS AND ACTIVE MATRIX LIQUID
Title Line Six:: CRYSTAL DEVICES
Total Drawing Sheets:: 10
Docket Number:: 038839.02

Continuity Information

>This application is a:: Division of
Application One:: 09/400,303
Filing Date:: September 21, 1999
Patent Number::
which is a:: Division of
>>Application Two:: 08/776,545
Filing Date:: January 31, 1997
Patent Number:: 6,066,516

Prior Foreign Applications

Foreign Application One:: 7-159147
Filing Date:: June 26, 1995
Country:: Japan
Priority Claimed:: Yes
Foreign Application Two:: 8-161280
Filing Date:: June 21, 1996
Country:: Japan
Priority Claimed:: Yes

Assignee Information

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